

## P-Channel 30 V (D-S) MOSFET

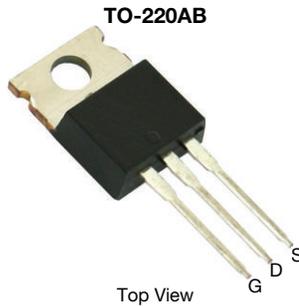
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A) <sup>d</sup>	Q <sub>g</sub> (TYP.)
-30	0.0087 at V <sub>GS</sub> = -10 V	-45	60
	0.0150 at V <sub>GS</sub> = -4.5 V	-45	

### FEATURES

- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

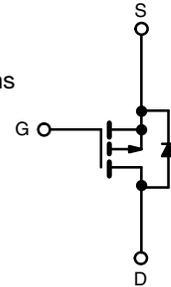


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



### APPLICATIONS

- Power switch
- Load switch in high current applications
- DC/DC converters



P-Channel MOSFET

### Ordering Information:

SUP45P03-09-GE3 (lead (Pb)-free and halogen-free)

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>d</sup>	T <sub>C</sub> = 25 °C	-45	A
	T <sub>C</sub> = 70 °C	-45	
Pulsed Drain Current (t = 100 μs)	I <sub>DM</sub>	-100	
Avalanche Current	I <sub>AS</sub>	-35	
Single Avalanche Energy <sup>a</sup>	E <sub>AS</sub>	61	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	73.5 <sup>b</sup>	W
	T <sub>A</sub> = 25 °C <sup>c</sup>	3.1	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	1.7	

### Notes

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).
- Package limited.



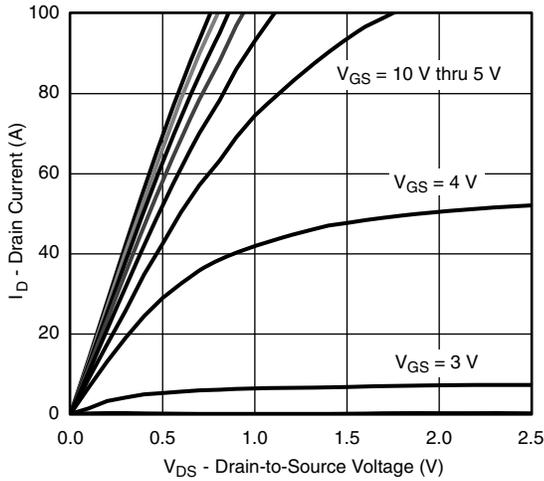
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1	-	-2.5	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 250	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	-	-	-1	μA
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	-50	
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C	-	-	-250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -10 V, V <sub>GS</sub> = -10 V	-50	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -20 A	-	0.0072	0.0087	Ω
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -15 A	-	0.0125	0.0150	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -20 A	-	45	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -15 V, f = 1 MHz	-	2700	-	pF
Output Capacitance	C <sub>oss</sub>		-	515	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	445	-	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -20 A	-	60	90	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		-	9.3	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	15	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.5	2.5	5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≅ -10 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 1 Ω	-	12	20	ns
Rise Time <sup>c</sup>	t <sub>r</sub>		-	11	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		-	40	60	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	12	20	
<b>Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (T<sub>C</sub> = 25 °C)</b>						
Continuous Current	I <sub>S</sub>		-	-	-45	A
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	-100	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = -10 A, V <sub>GS</sub> = 0 V	-	-0.8	-1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -10 A, di/dt = 100 A/μs	-	27	40	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>		-	1.3	2	A
Reverse Recovery Charge	Q <sub>rr</sub>		-	20	30	nC

**Notes**

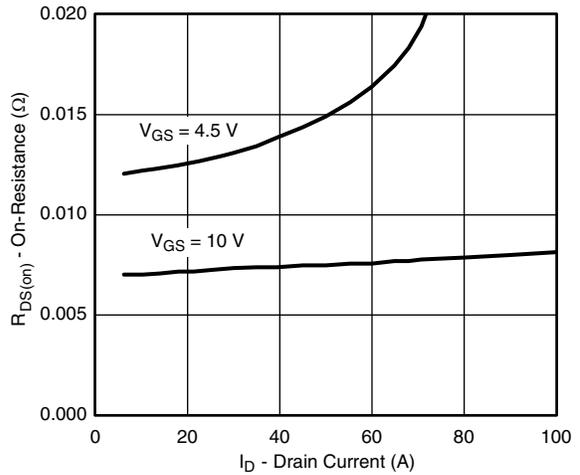
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

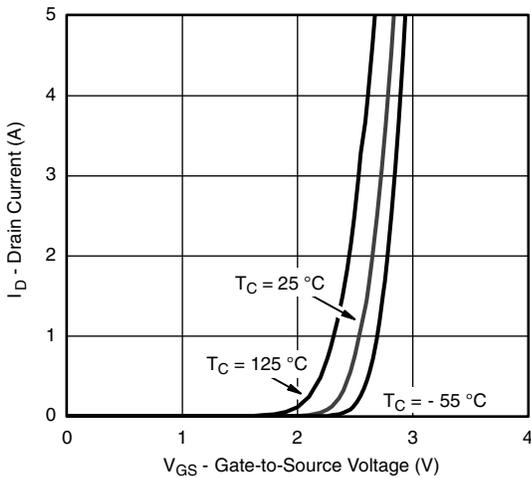
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



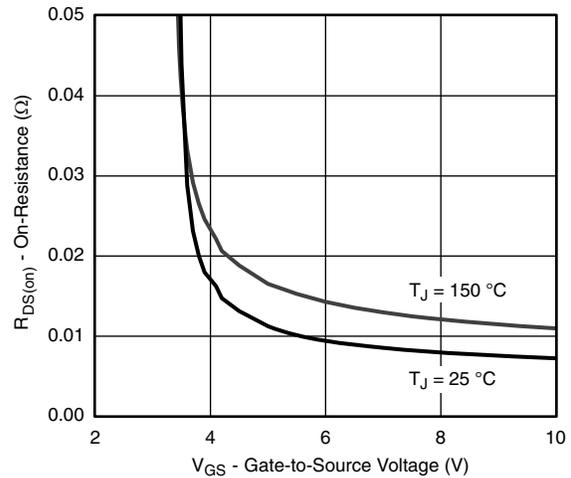
**Output Characteristics**



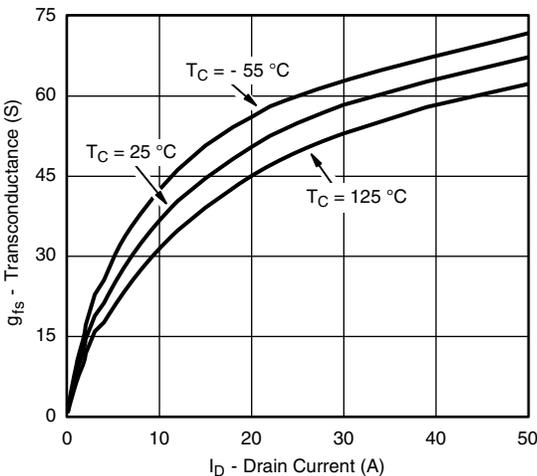
**On-Resistance vs. Drain Current**



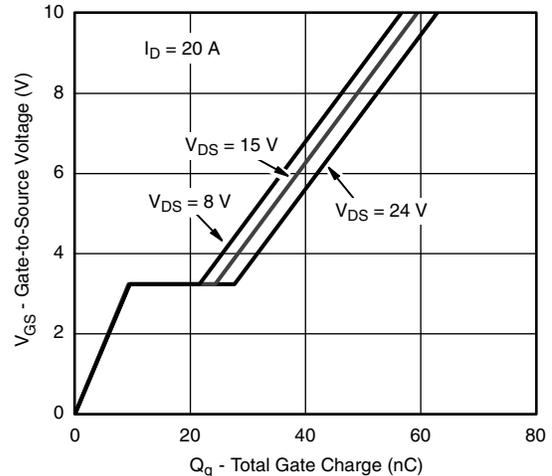
**Transfer Characteristic**



**On-Resistance vs. Gate-to-Source Voltage**

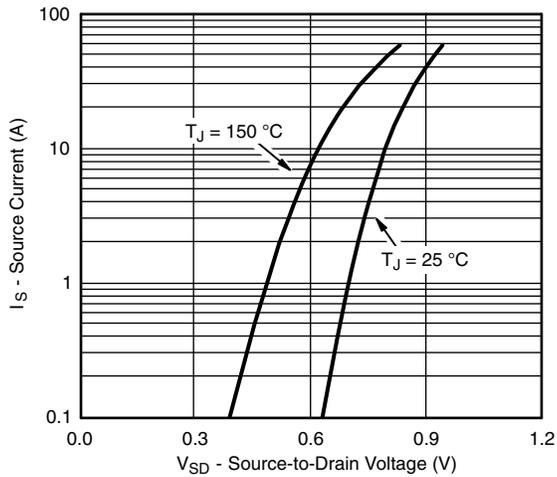


**Transconductance**

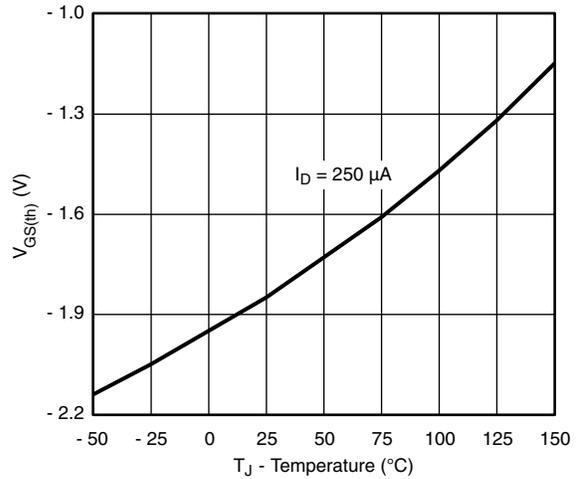


**Gate Charge**

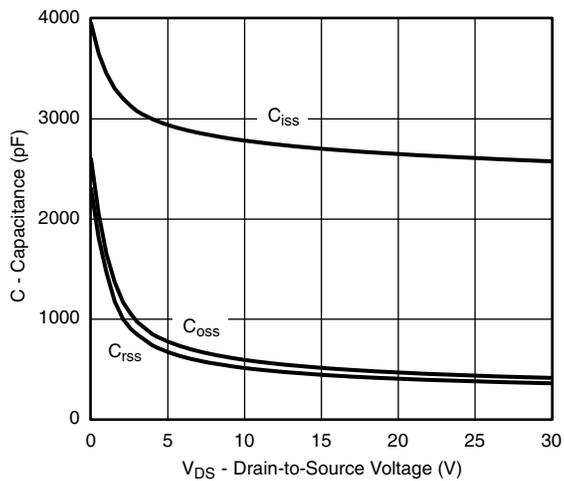
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



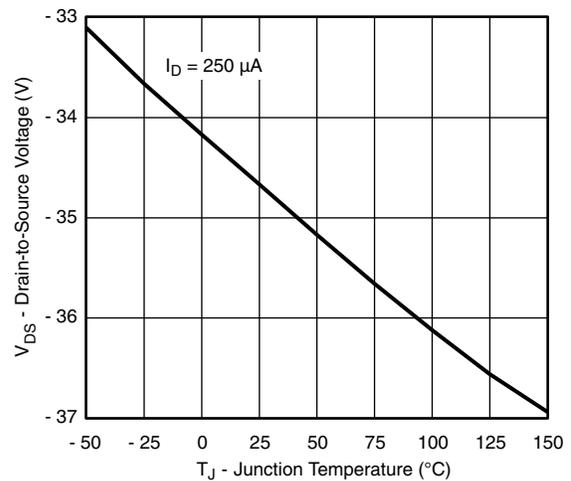
**Source-Drain Diode Forward Voltage**



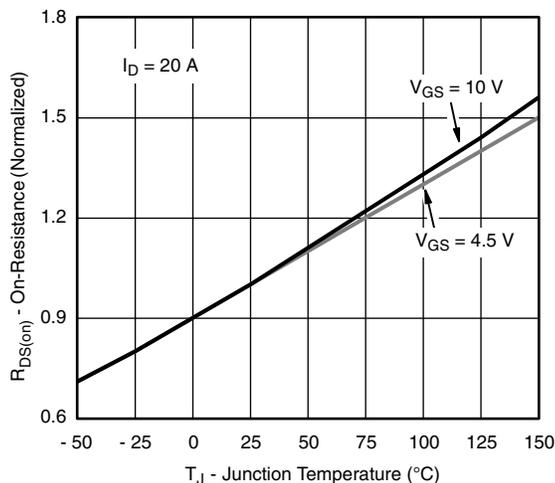
**Threshold Voltage**



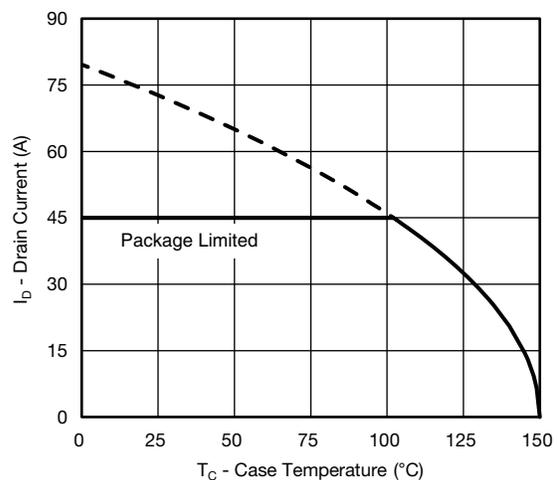
**Capacitance**



**Drain Source Breakdown vs. Junction Temperature**



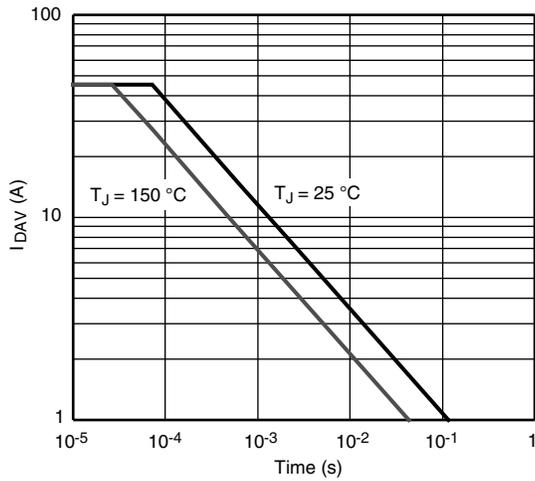
**On-Resistance vs. Junction Temperature**



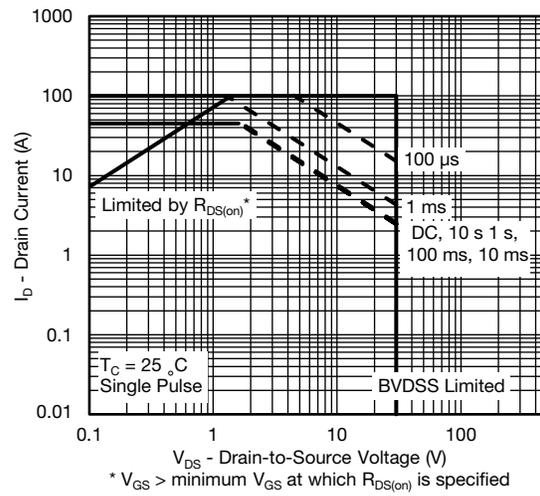
**Current Derating**



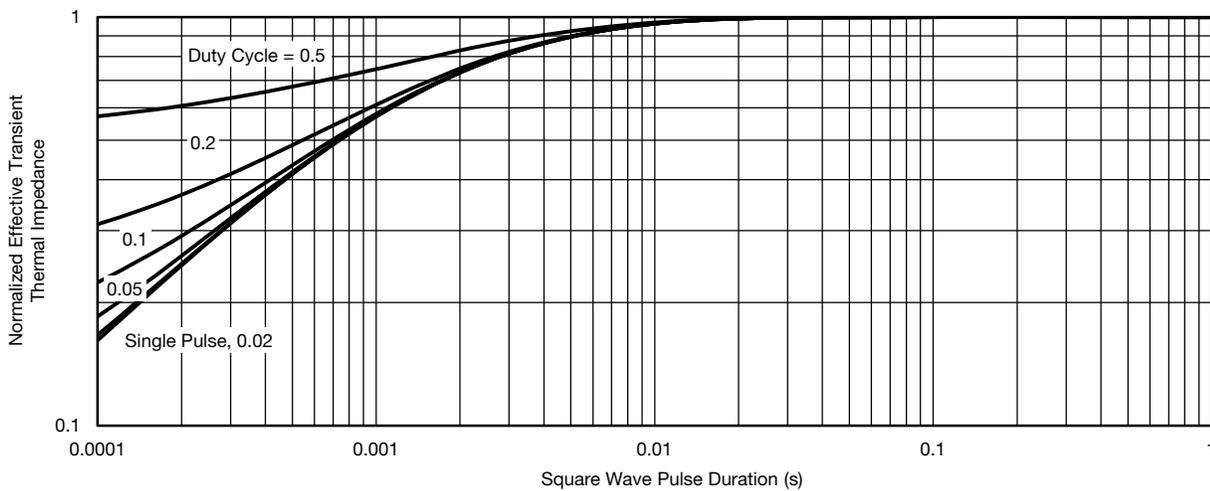
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time



Safe Operating Area

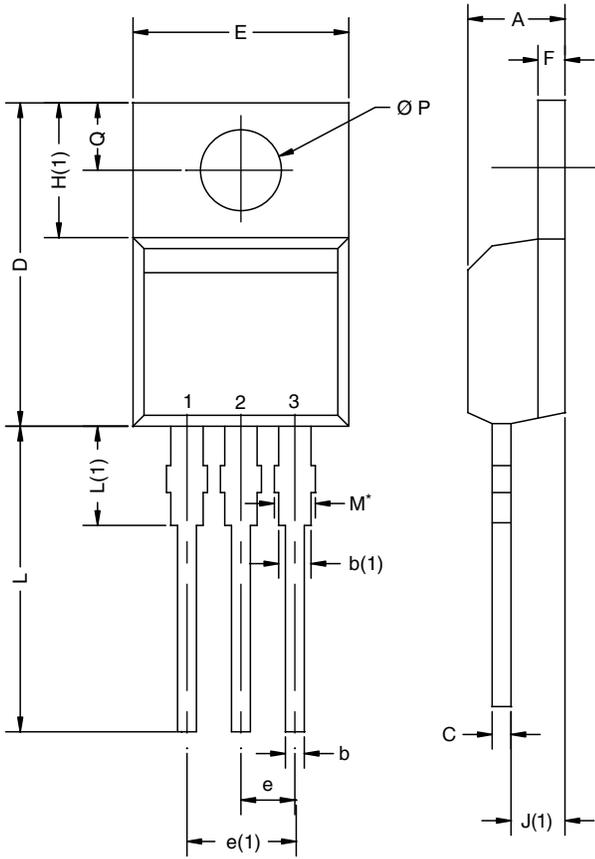


Normalized Thermal Transient Impedance, Junction-to-Case

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TO-220AB

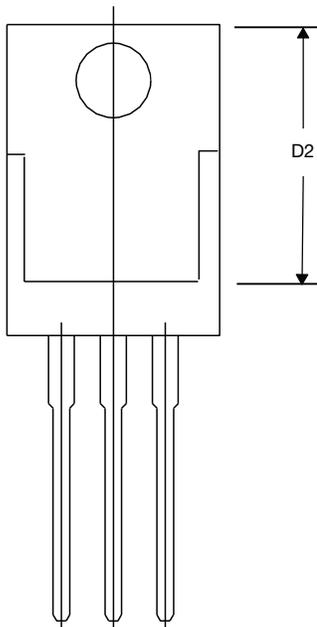


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T14-0413-Rev. P, 16-Jun-14  
DWG: 5471

Note

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM





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